# PDTC114E series

# NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

Rev. 12 — 21 December 2011

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

NPN Resistor-Equipped Transistor (RET) family in small Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

| Type number | Package | cage   |          | PNP        | Package              |  |
|-------------|---------|--------|----------|------------|----------------------|--|
|             | NXP     | JEITA  | JEDEC    | complement | configuration        |  |
| PDTC114EE   | SOT416  | SC-75  | -        | PDTA114EE  | ultra small          |  |
| PDTC114EM   | SOT883  | SC-101 | -        | PDTA114EM  | leadless ultra small |  |
| PDTC114ET   | SOT23   | -      | TO-236AB | PDTA114ET  | small                |  |
| PDTC114EU   | SOT323  | SC-70  | -        | PDTA114EU  | very small           |  |

#### 1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

#### 1.3 Applications

- Digital application in automotive and industrial segments
- Control of IC inputs

- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

#### 1.4 Quick reference data

Table 2. Quick reference data

| Symbol    | Parameter                 | Conditions | Min | Тур | Max | Unit |
|-----------|---------------------------|------------|-----|-----|-----|------|
| $V_{CEO}$ | collector-emitter voltage | open base  | -   | -   | 50  | V    |
| Io        | output current            |            | -   | -   | 100 | mA   |
| R1        | bias resistor 1 (input)   |            | 7   | 10  | 13  | kΩ   |
| R2/R1     | bias resistor ratio       |            | 0.8 | 1.0 | 1.2 |      |



top view

### 2. Pinning information

Table 3. **Pinning** Pin Simplified outline **Graphic symbol Description** SOT23; SOT323; SOT416 1 input (base) 3 2 GND (emitter) 3 output (collector) 2 006aaa144 sym007 **SOT883** 1 input (base) 2 GND (emitter) output (collector) Transparent

### 3. Ordering information

Table 4. Ordering information

| Type number | Package |   |         |  |  |  |  |
|-------------|---------|---|---------|--|--|--|--|
|             | Name    | Description   | Version |  |  |  |  |
| PDTC114EE   | SC-75   | plastic surface-mounted package; 3 leads  | SOT416  |  |  |  |  |
| PDTC114EM   | SC-101  | leadless ultra small plastic package; 3 solder lands; body 1.0 $\times$ 0.6 $\times$ 0.5 mm | SOT883  |  |  |  |  |
| PDTC114ET   | -       | plastic surface-mounted package; 3 leads  | SOT23   |  |  |  |  |
| PDTC114EU   | SC-70   | plastic surface-mounted package; 3 leads  | SOT323  |  |  |  |  |

### 4. Marking

Table 5. Marking codes

| Type number | Marking code <sup>[1]</sup> |
|-------------|-----------------------------|
| PDTC114EE   | 09                          |
| PDTC114EM   | DS                          |
| PDTC114ET   | *16                         |
| PDTC114EU   | *09                         |

<sup>[1] \* =</sup> placeholder for manufacturing site code.

### 5. Limiting values

Table 6. Limiting values

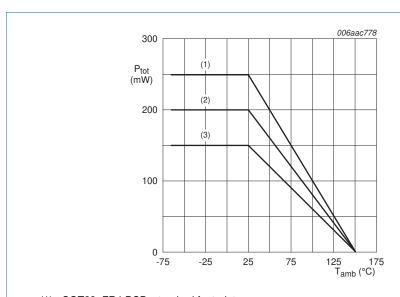
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                 | Conditions                   | Min          | Max  | Unit |
|------------------|---------------------------|------------------------------|--------------|------|------|
| $V_{\text{CBO}}$ | collector-base voltage    | open emitter                 | -            | 50   | V    |
| $V_{CEO}$        | collector-emitter voltage | open base                    | -            | 50   | V    |
| $V_{EBO}$        | emitter-base voltage      | open collector               | -            | 10   | V    |
| VI               | input voltage             |                              |              |      |      |
|                  | positive                  |                              | -            | +40  | V    |
|                  | negative                  |                              | -            | -10  | V    |
| Io               | output current            |                              | -            | 100  | mA   |
| I <sub>CM</sub>  | peak collector current    | single pulse; $t_p \le 1$ ms | -            | 100  | mA   |
| P <sub>tot</sub> | total power dissipation   | $T_{amb} \le 25  ^{\circ}C$  |              |      |      |
|                  | PDTC114EE (SOT416)        |                              | [1][2]       | 150  | mW   |
|                  | PDTC114EM (SOT883)        |                              | [2][3]       | 250  | mW   |
|                  | PDTC114ET (SOT23)         |                              | <u>[1]</u> - | 250  | mW   |
|                  | PDTC114EU (SOT323)        |                              | <u>[1]</u> - | 200  | mW   |
| Tj               | junction temperature      |                              | -            | 150  | °C   |
| T <sub>amb</sub> | ambient temperature       |                              | -65          | +150 | °C   |
| T <sub>stg</sub> | storage temperature       |                              | -65          | +150 | °C   |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

<sup>[3]</sup> Device mounted on an FR4 PCB with 70  $\mu m$  copper strip line, standard footprint.



- (1) SOT23; FR4 PCB, standard footprint SOT883; FR4 PCB with 70  $\mu m$  copper strip line, standard footprint
- (2) SOT323; FR4 PCB, standard footprint
- (3) SOT416; FR4 PCB, standard footprint

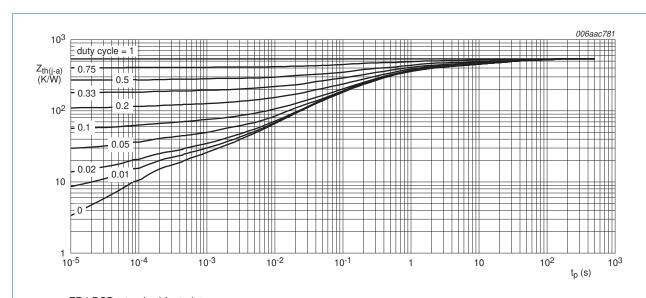
Fig 1. Power derating curves

#### 6. Thermal characteristics

Table 7. Thermal characteristics

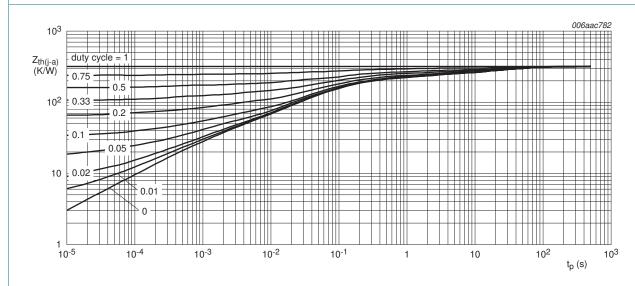
| Symbol        | Parameter                                   | Conditions  | Min          | Тур | Max | Unit |
|---------------|---|-------------|--------------|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air |              |     |     |      |
|               | PDTC114EE (SOT416)                          |             | [1][2]       | -   | 830 | K/W  |
|               | PDTC114EM (SOT883)                          |             | [2][3]       | -   | 500 | K/W  |
|               | PDTC114ET (SOT23)                           |             | [1] -        | -   | 500 | K/W  |
|               | PDTC114EU (SOT323)                          |             | <u>[1]</u> - | -   | 625 | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB with 70  $\mu m$  copper strip line, standard footprint.



FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC114EE (SOT416); typical values



FR4 PCB, 70 µm copper strip line

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC114EM (SOT883); typical values

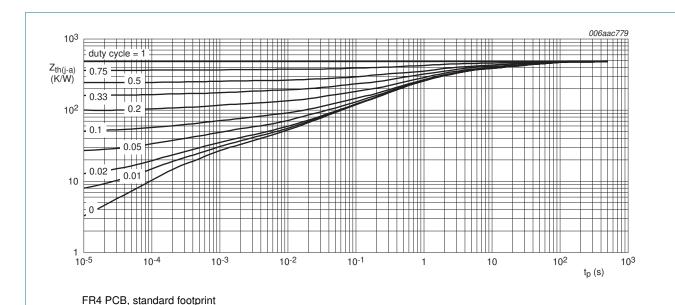


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC114ET (SOT23); typical values

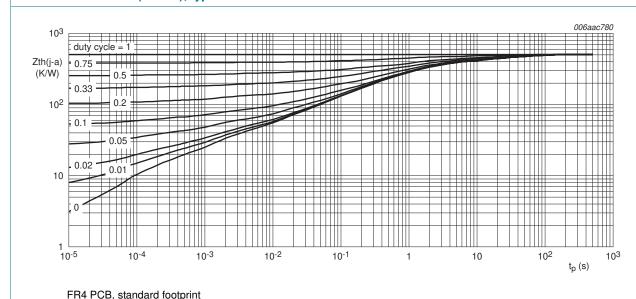


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC114EU (SOT323); typical values

NPN resistor-equipped transistors; R1 = 10 kΩ, R2 = 10 kΩ

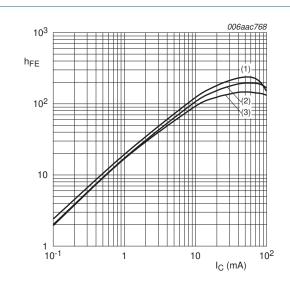
### 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

| · anno — -         |                                      |   |       |     |     |      |
|--------------------|--------------------------------------|---|-------|-----|-----|------|
| Symbol             | Parameter                            | Conditions  | Min   | Тур | Max | Unit |
| I <sub>CBO</sub>   | collector-base<br>cut-off current    | $V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$                                      | -     | -   | 100 | nA   |
| I <sub>CEO</sub>   | collector-emitter<br>cut-off current | $V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$                                    | -     | -   | 1   | μΑ   |
|                    |                                      | $V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$<br>$T_{j} = 150 ^{\circ}\text{C}$ | -     | -   | 5   | μΑ   |
| I <sub>EBO</sub>   | emitter-base<br>cut-off current      | $V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$                                     | -     | -   | 400 | μΑ   |
| h <sub>FE</sub>    | DC current gain                      | $V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$                                    | 30    | -   | -   |      |
| V <sub>CEsat</sub> | collector-emitter saturation voltage | $I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$                                     | -     | -   | 150 | mV   |
| $V_{I(off)}$       | off-state input<br>voltage           | $V_{CE} = 5 \text{ V}; I_C = 100 \mu\text{A}$                                   | -     | 1.1 | 8.0 | V    |
| $V_{I(on)}$        | on-state input<br>voltage            | $V_{CE} = 0.3 \text{ V}; I_{C} = 10 \text{ mA}$                                 | 2.5   | 1.8 | -   | V    |
| R1                 | bias resistor 1 (input)              |   | 7     | 10  | 13  | kΩ   |
| R2/R1              | bias resistor ratio                  |   | 0.8   | 1.0 | 1.2 |      |
| C <sub>c</sub>     | collector capacitance                | $V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz                     | -     | -   | 2.5 | pF   |
| f <sub>T</sub>     | transition frequency                 | $V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz                      | [1] - | 230 | -   | MHz  |
|                    |                                      |   |       |     |     |      |

<sup>[1]</sup> Characteristics of built-in transistor.



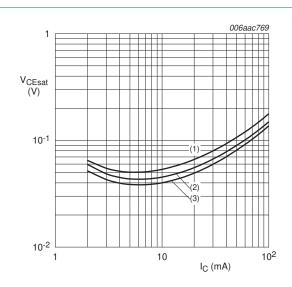
$$V_{CE} = 5 \text{ V}$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig 6. DC current gain as a function of collector current; typical values



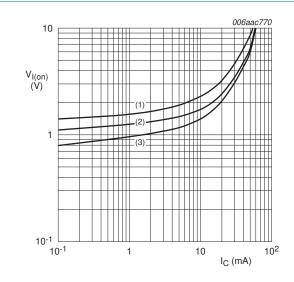
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



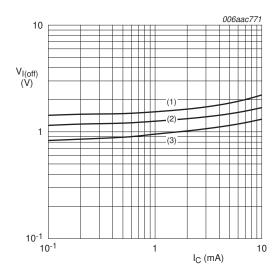
$$V_{CE} = 0.3 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 8. On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 9. Off-state input voltage as a function of collector current; typical values

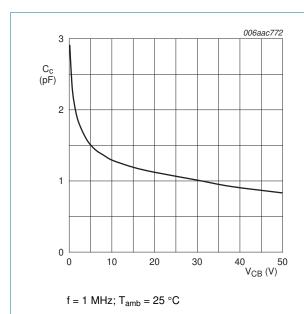


Fig 10. Collector capacitance as a function of collector-base voltage; typical values

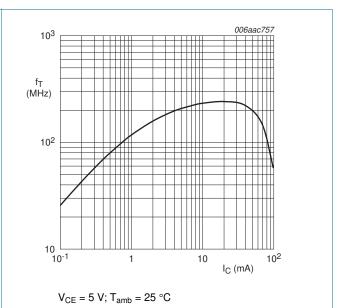


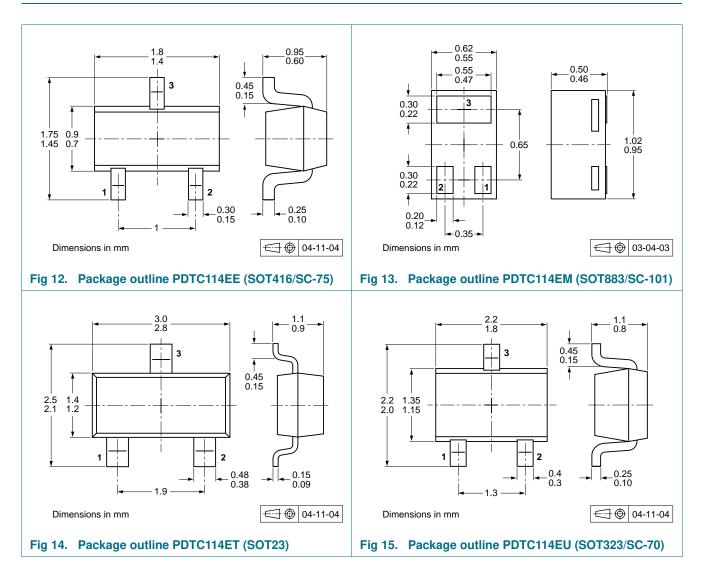
Fig 11. Transition frequency as a function of collector current; typical values of built-in transistor

#### 8. Test information

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 9. Package outline



### 10. Packing information

Table 9. Packing methods

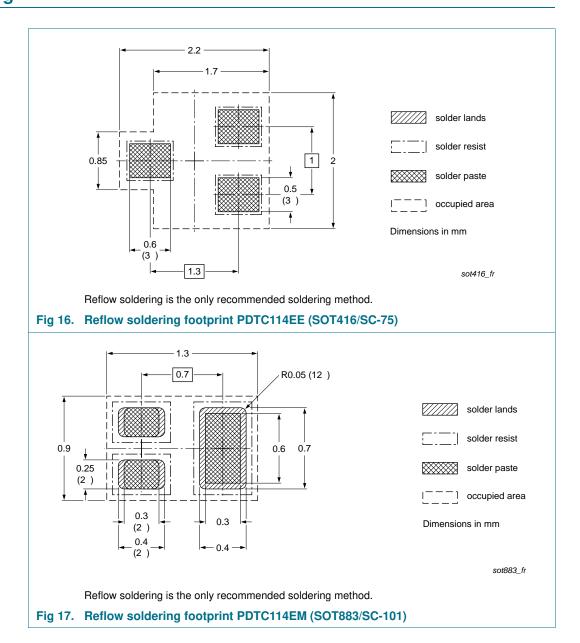
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

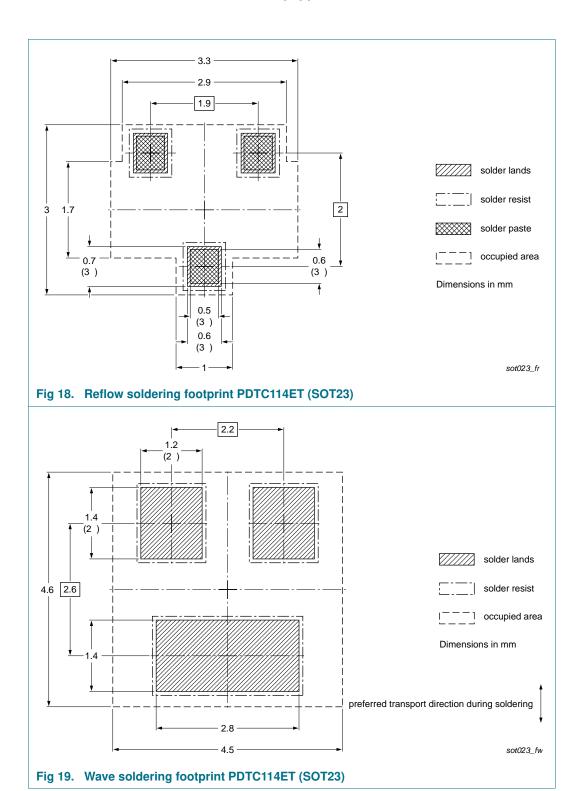
| Type number | Package | Description                    | Packing | Packing quantity |  |  |
|-------------|---------|--------------------------------|---------|------------------|--|--|
|             |         |                                | 3000    | 10000            |  |  |
| PDTC114EE   | SOT416  | 4 mm pitch, 8 mm tape and reel | -115    | -135             |  |  |
| PDTC114EM   | SOT883  | 2 mm pitch, 8 mm tape and reel | -       | -315             |  |  |
| PDTC114ET   | SOT23   | 4 mm pitch, 8 mm tape and reel | -215    | -235             |  |  |
| PDTC114EU   | SOT323  | 4 mm pitch, 8 mm tape and reel | -115    | -135             |  |  |

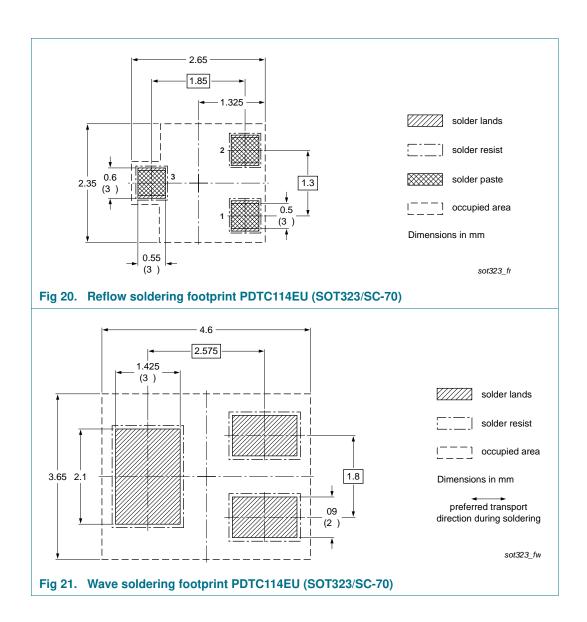
<sup>[1]</sup> For further information and the availability of packing methods, see  $\underline{\text{Section 14}}$ .

PDTC114E\_SER

### 11. Soldering







NPN resistor-equipped transistors; R1 = 10 kΩ, R2 = 10 kΩ

### 12. Revision history

#### Table 10. Revision history

| Document ID          | Release date   | Data sheet status      | Change notice | Supersedes           |
|----------------------|----------------|------------------------|---------------|----------------------|
| PDTC114E_SER v.12    | 20111221       | Product data sheet     | -             | PDTC114E_SER v.11    |
| Modifications:       | • Figure 3 and | d <u>5</u> : corrected |               |                      |
| PDTC114E_SER v.11    | 20111121       | Product data sheet     | -             | PDTC114E_SERIES v.10 |
| PDTC114E_SERIES v.10 | 20040805       | Product specification  | -             | PDTC114E_SERIES v.9  |
| PDTC114E_SERIES v.9  | 20030410       | Product specification  | -             | -                    |

### 13. Legal information

#### 13.1 Data sheet status

| Document status[1][2]          | Product status[3] | Definition  |
|--------------------------------|-------------------|---|
| Objective [short] data sheet   | Development       | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification     | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production        | This document contains the product specification.                                     |

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- [2] The term 'short data sheet' is explained in section "Definitions"
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PDTC114E SER

## **PDTC114E series**

NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$ 

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# **PDTC114E series**

NPN resistor-equipped transistors; R1 = 10 kΩ, R2 = 10 kΩ

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